

Product Overview

FDMS4D0N12C: N-Channel Shielded Gate PowerTrench® MOSFET 120V, 118A, 4.0mΩ

For complete documentation, see the data sheet.

This N-Channel MV MOSFET is produced using an advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 4.0 mΩ at $V_{GS} = 10$ V, $I_D = 67$ A
- Max $r_{DS(on)}$ = 8.0 mΩ at $V_{GS} = 6$ V, $I_D = 33$ A
- 50% Lower Q_{rr} than Other MOSFET Suppliers
- Lowers Switching Noise/EMI
- MSL1 Robust Package Design
- 100% UIL Tested
- RoHS Compliant

Applications

- This product is general usage and suitable for many different applications.

End Products

- AC-DC and DC-DC Power Supplies

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	V_{GS}^{Max} (V)	$V_{GS}^{(th)}$ Max (V)	I_D^{Max} (A)	P_D^{Max} (W)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 2.5$ V (mΩ)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 4.5$ V (mΩ)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 10$ V (mΩ)	Q_g^{Typ} @ $V_{GS} = 4.5$ V (nC)	Q_g^{Typ} @ $V_{GS} = 10$ V (nC)	C_{iss}^{Typ} (pF)	Package Type
FDMS4D0N12C	1.5301	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	120	+20V	4	118	2.7			4		58	4565	PQFN-8

For more information please contact your local sales support at www.onsemi.com.

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